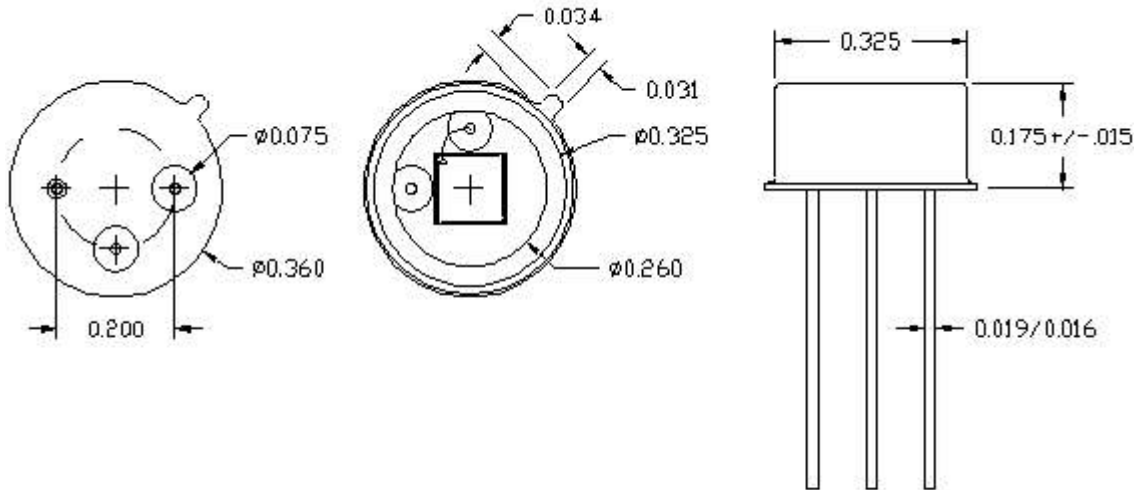


**DESCRIPTION**

This is a large area Silicon detector optimized for applications requiring high Responsivity and high reliability.

**FEATURES**

- High Speed and high Responsivity
- Large Active Area, 0.110" x 0.110" square
- High Reliability Hermetic TO-5 Package
- Similar to FFD-100 and TOX 9103 devices



**ABSOLUTE MAXIMUM RATINGS**

- Storage temperature..... -65°C to +125°C
- Case operating temperature..... -55°C to +100°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 45 Volts

**OUTLINE DIMENSIONS**

Tolerances are +/-0.005 inches, except as noted

Pin 1 - Anode, Pin 2 Cathode, Pin 3 Case (Cathode)

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	$I_r = 30 \mu A, H = 0 \text{ mW}$	$V_{BR}$	45	240		Volts
Responsivity	$H = 10 \mu W, V_r = 5 \text{ Volts}$ $\lambda = 900 \text{ nm}$	$R_c$	.45	.55		A/W
Dark Current	$V_r = 20 \text{ Volts}, H = 0 \text{ mW}$	$I_d$		5	30	nA
Response Time	10%-90%, $V_r = 5 \text{ Volts}$ $R_l = 50 \Omega$	$t_r$ $t_f$		5 5		nsec nsec
Spectral Response		$\lambda$	400		1100	nm
Capacitance	$V_r = 5V, f = 1 \text{ MHz}$	$C$		17		pF
Forward Voltage	$I_f = 20 \text{ mA}$	$V_f$		0.9	1.1	Volts

**ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)**

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